



Handwritten: #4/8/02 Andy D. Dorian 6-10-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No.: LSI.08USC1 (95-133/1P/1C/1D)

Applicant: Bartlett, et al.

Appl. No.: 09/991,277 ✓

Examiner: David S. Blum

Filed: November 9, 2001

Group Art Unit: 2813

Title: CIRCUIT ISOLATION UTILIZING MeV IMPLANTATION

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Assistant Commissioner for Patents

Washington, DC 20231

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PRELIMINARY AMENDMENT

Dear Sir:

Prior to examination, please amend the above-identified application as follows:

In the Claims: ✓

Please amend claims 1, 2, and 7 as follows:

1. (Amended) An integrated circuit having a plurality of circuits formed on a common substrate that are isolated by isolation regions in said common substrate between said circuits, said integrated circuit made by the process of:

masking predetermined locations of said common substrate that are aligned with said isolation regions with a material that is capable of masking high energy ions;

irradiating said common substrate with said high energy ions such that said high energy ions have an energy level sufficient to implant said high energy ions in embedded regions of said common substrate that have a lower resistance than said common substrate and that are substantially aligned with unmasked portions of said common substrate that are substantially aligned with said circuits so that said isolation regions having a higher resistance than said common substrate are formed in said common substrate between said embedded regions and said embedded regions are buried

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